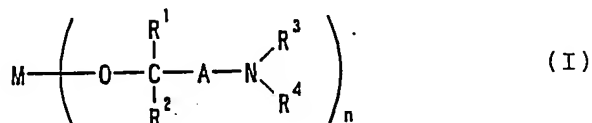


AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings of claims in the application:

LISTING OF CLAIMS:

1.(original) A metal compound represented by general formula (I):



wherein R¹, R², R³, and R⁴ each represent an alkyl group having 1 to 4 carbon atoms; A represents an alkanediyl group having 1 to 8 carbon atoms; M represents a lead atom, a titanium atom or a zirconium atom; n represents 2 when M is a lead atom or 4 when M is a titanium or zirconium atom.

2.(original) The metal compound according to claim 1, wherein A is a methylene group.

3.(currently amended) The metal compound according to claim 1 [[or 2]], wherein M is a lead atom.

4.(currently amended) The metal compound according to claim 1 [[or 2]], wherein M is a titanium atom.

5.(currently amended) The metal compound according to claim 1 [[or 2]], wherein M is a zirconium atom.

6.(currently amended) A material for thin film formation comprising the metal compound according to ~~any one of claims 1 to 5~~ claim 1.

7.(currently amended) A material for thin film formation comprising ~~the metal compound of claim 3, the metal compound of claim 4, and the metal compound of claim 5~~ a metal compound of formula (I), wherein M is a lead atom; a compound of formula (I), wherein M is a titanium atom; and a compound of formula (I), wherein M is a zirconium atom; and wherein the compound of formula (I) is the compound according to claim 1.

8.(original) A material for thin film formation comprising the metal compound of claim 3, tetrakis(1-methoxy-2-methyl-2-propoxy)titanium, and tetrakis(1-methoxy-2-methyl-2-propoxy)zirconium.

9.(currently amended) A process for thin film formation comprising vaporizing the material for thin film formation according to claim 6, [[7 or 8,]] introducing the resulting vapor containing the metal compound onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

10.(currently amended) A process for thin film formation comprising vaporizing a material for thin film formation containing the metal compound of claim 3, ~~a material for thin film formation containing the metal compound of claim 4, and a material for thin film formation containing the metal compound of claim 5~~ to obtain vapor containing the metal compounds, introducing the resulting vapor containing the metal compounds onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

11.(new) A process for thin film formation comprising vaporizing a material for thin film formation containing the metal compound of claim 3, a material for thin film formation containing

tetrakis(1-methoxy-2-methyl-2-propoxy)titanium, and a material for thin film formation containing tetrakis(1-methoxy-2-methyl-2-propoxy)zirconium to obtain vapor containing the metal compounds, introducing the resulting vapor containing the metal compounds onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

12.(original) A process for thin film formation comprising vaporizing a material for thin film formation containing the metal compound of claim 3, a material for thin film formation containing tetra(tert-butoxy)titanium, and a material for thin film formation containing tetra(tert-butoxy)zirconium to obtain vapor containing the metal compounds, introducing the resulting vapor containing the metal compounds onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

13.(new) A process for thin film formation comprising vaporizing a material for thin film formation containing the metal compound of claim 4, to obtain vapor containing the metal compounds, introducing the resulting vapor containing the metal compounds onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

14.(new) A process for thin film formation comprising vaporizing a material for thin film formation containing the metal compound of claim 5, to obtain vapor containing the metal compounds, introducing the resulting vapor containing the metal compounds onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

15.(new) A process for thin film formation comprising vaporizing the material for thin film formation according to claim 7, introducing the resulting vapor containing the metal compound onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

16.(new) A process for thin film formation comprising vaporizing the material for thin film formation according to claim 8, introducing the resulting vapor containing the metal compound onto a substrate, and causing the vapor to decompose and/or chemically react to form a metal-containing thin film on the substrate.

17.(new) The metal compound according to claim 2, wherein M is a lead atom.

18.(new) The metal compound according to claim 2, wherein M is a titanium atom.

19.(new) The metal compound according to claim 2, wherein M is a zirconium atom.